

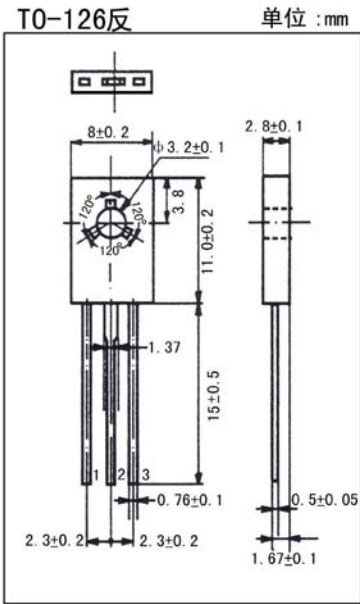
MJE13003HK5 (3DD13003HK5)硅 NPN 半导体三极管/SILICON NPN TRANSISTOR

用途：主要用于节能灯、日光灯电子镇流器及其它开关、振荡电路。

Purpose: High frequency electronic lighting ballast applications, converters, inverters, switching regulators, etc.

极限参数/Absolute maximum ratings(Ta=25℃)

参数符号 Symbol	数值 Rating	单位 Unit
V _{CB0}	900	V
V _{CE0}	530	V
V _{EB0}	9.0	V
I _C	1.2	A
I _{CP}	3.0	A
P _C (Ta=25℃)	1.25	W
P _C (Tc=25℃)	50	W
T _j	150	℃
T _{stg}	-55~150	℃



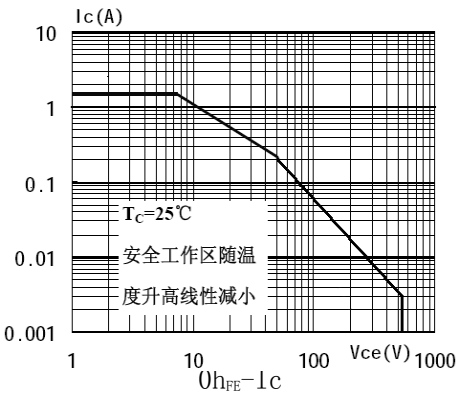
引脚：1. B 2. C 3. E

电性能参数/Electrical characteristics(Ta=25℃)

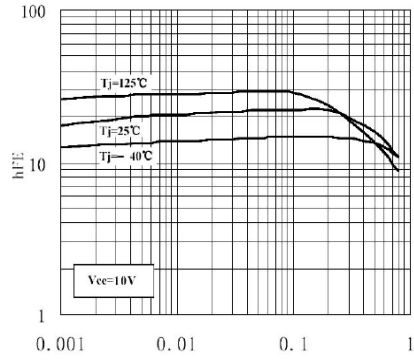
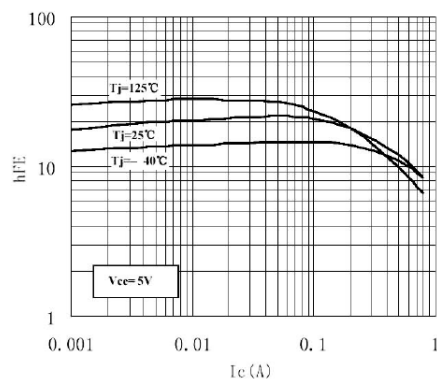
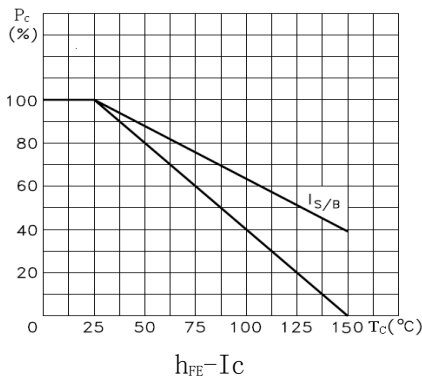
参数符号 Symbol	测试条件 Test condition		数值 Rating			单位 Unit
			最小值 Min	典型值 Typ	最大值 Max	
V _{CB0}	I _C =1mA	I _E =0	900			V
V _{CE0}	I _C =10mA	I _B =0	530			V
V _{EB0}	I _E =1mA	I _C =0	9.0			V
I _{CB0}	V _{CB} =900V	I _E =0			0.1	mA
I _{CE0}	V _{CE} =530V	I _B =0			0.1	mA
I _{EB0}	V _{EB} =9.0V	I _C =0			0.1	mA
h _{FE(1)}	V _{CE} =10V	I _C =0.2A	10		40	
h _{FE(2)}	V _{CE} =10V	I _C =10uA	15			
h _{FE(3)}	V _{CE} =10V	I _C =1.0A	6		40	
V _{CE(sat)}	I _C =0.5A	I _B =0.1A			0.8	V
V _{BE(sat)}	I _C =0.5A	I _B =0.1A			1.2	V
f _T	V _{CE} =10V	I _C =0.1A	f=1.0MHz	5.0		MHz
t _f	V _{CE} =5V I _C =0.25A (UI9600)				1.2	μs
t _S					5.0	μs

MJE13003HK5 (3DD13003HK5)

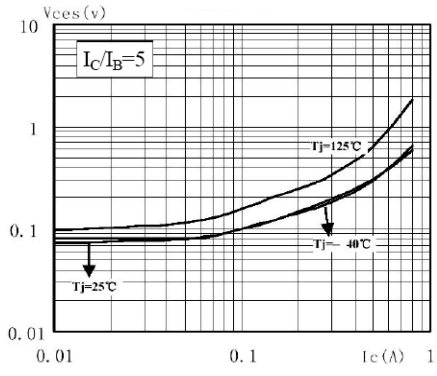
SOA (DC)



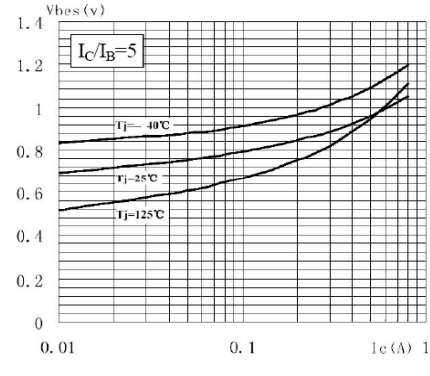
$P_C - T_C$



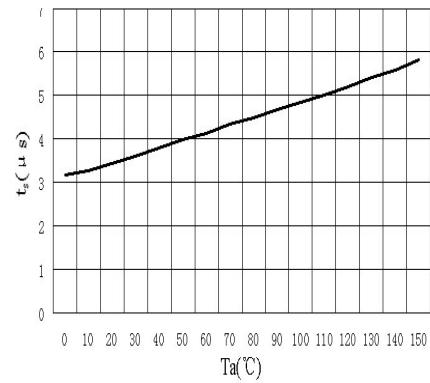
$V_{CES} - I_C$



$V_{BES} - I_C$



$t_s - T_a$



$h_{FE} - T_a$

